

Bipolar Transistor

(-)100 V, (-)1 A, Low $V_{CE(sat)}$,
(PNP)NPN Single PCP

2SA1416, 2SC3646

Features

- Adoption of FBET and MBIT Processes
- High Breakdown Voltage and Large Current Capacity
- Fast Switching Speed
- Ultrasmall Size Making it Easy to Provide High-Density Small-Sized Hybrid IC's
- These Devices are Pb-Free and are RoHS Compliant

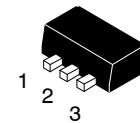
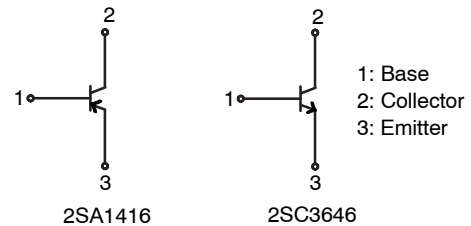
SPECIFICATIONS (): 2SA1416
ABSOLUTE MAXIMUM RATINGS at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Collector to Base Voltage	V_{CBO}	(-) 120	V
Collector to Emitter Voltage	V_{CEO}	(-) 100	V
Emitter to Base Voltage	V_{EBO}	(-) 6	V
Collector Current	I_C	(-) 1	A
Collector Current (Pulse)	I_{CP}	(-) 2	A
Collector Dissipation	P_C	500	mW
Collector Dissipation (Note 1)		1.3	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

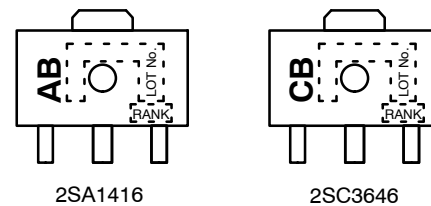
1. Surface mounted on ceramic substrate (250 mm² x 0.8 mm).

ELECTRICAL CONNECTION



SOT-89 / PCP-1
CASE 419AU

MARKING DIAGRAM



ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

2SA1416, 2SC3646

ELECTRICAL CHARACTERISTICS at $T_A = 25^\circ\text{C}$

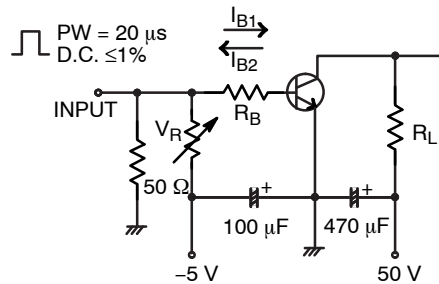
Parameter	Symbol	Conditions	Ratings			Unit
			Min	Typ	Max	
Collector Cutoff Current	I_{CBO}	$V_{CB} = (-)100\text{ V}$, $I_E = 0\text{ A}$			$(-)100$	nA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = (-)4\text{ V}$, $I_C = 0\text{ A}$			$(-)100$	nA
DC Current Gain	h_{FE}	$V_{CE} = (-)5\text{ V}$, $I_C = (-)100\text{ mA}$	100*		400*	
Gain-Bandwidth Product	f_T	$V_{CE} = (-)10\text{ V}$, $I_C = (-)100\text{ mA}$		120		MHz
Output Capacitance	C_{ob}	$V_{CB} = (-)10\text{ V}$, $f = 1\text{ MHz}$		(13)8.5		pF
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = (-)400\text{ mA}$, $I_B = (-)40\text{ mA}$		$(-0.2)0.1$	$(-0.6)0.4$	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = (-)400\text{ mA}$, $I_B = (-)40\text{ mA}$		$(-)0.85$	$(-)1.2$	V
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)10\text{ }\mu\text{A}$, $I_E = 0\text{ A}$	$(-)120$			V
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1\text{ mA}$, $R_{BE} = \infty$	$(-)100$			V
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)10\text{ }\mu\text{A}$, $I_C = 0\text{ A}$	$(-)6$			V
Turn-On Time	t_{on}	See specified Test Circuit		(80)80		ns
Storage Time	t_{stg}			(700)850		ns
Fall Time	t_f			(40)50		ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

*The 2SA1416/2SC3646 are classified by 100 mA h_{FE} as follows :

Rank	R	S	T
h_{FE}	100 to 200	140 to 280	200 to 400

Switching Time Test Circuit



$I_C = 10\text{ mA}$ $I_{B1} = -10\text{ mA}$ $I_{B2} = 400\text{ mA}$
(For PNP, the polarity is reversed)

TYPICAL CHARACTERISTICS

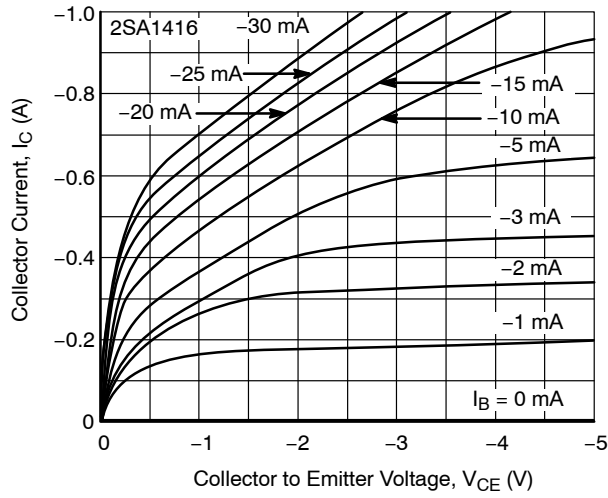


Figure 1. $I_C - V_{CE}$

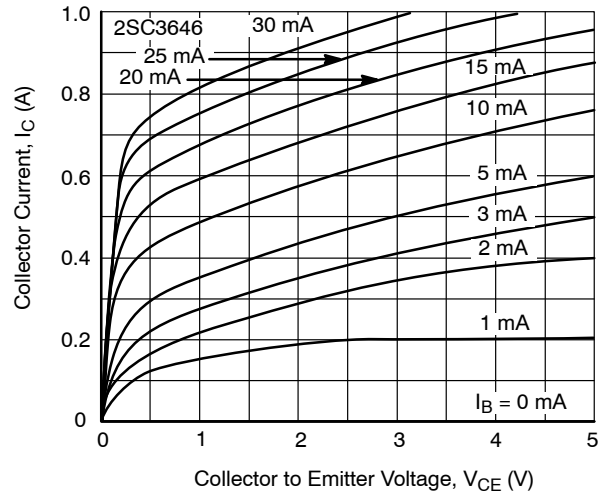


Figure 2. $I_C - V_{CE}$

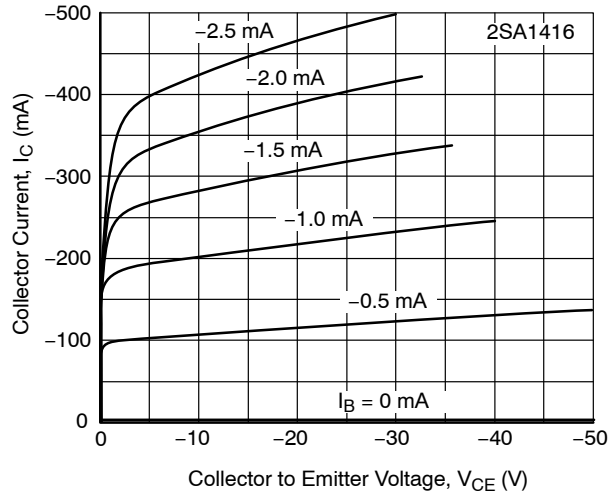


Figure 3. $I_C - V_{CE}$

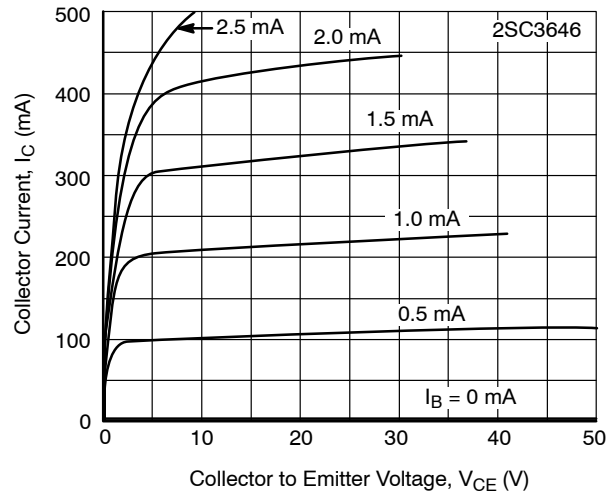


Figure 4. $I_C - V_{CE}$

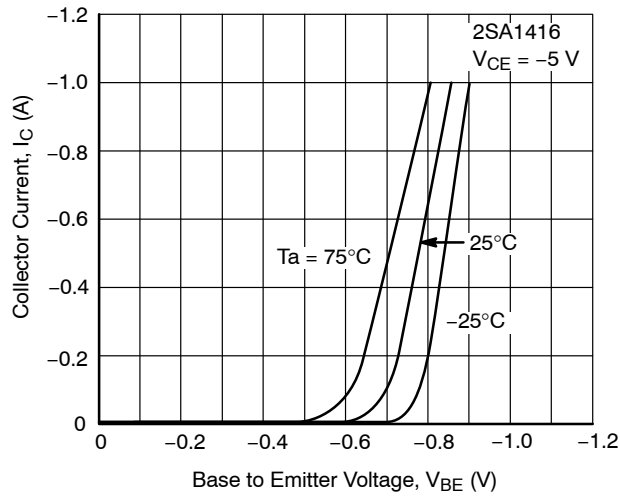


Figure 5. $I_C - V_{BE}$

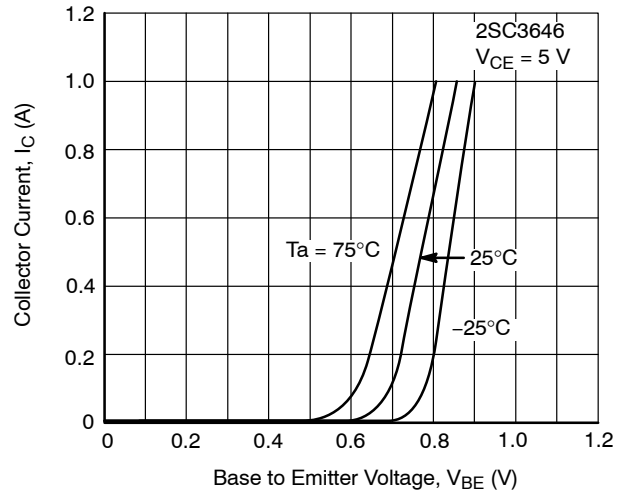


Figure 6. $I_C - V_{BE}$

2SA1416, 2SC3646

TYPICAL CHARACTERISTICS (continued)

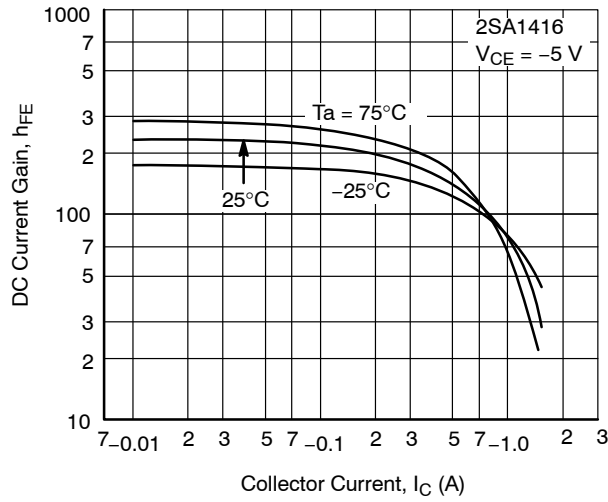


Figure 7. $h_{FE} - I_C$

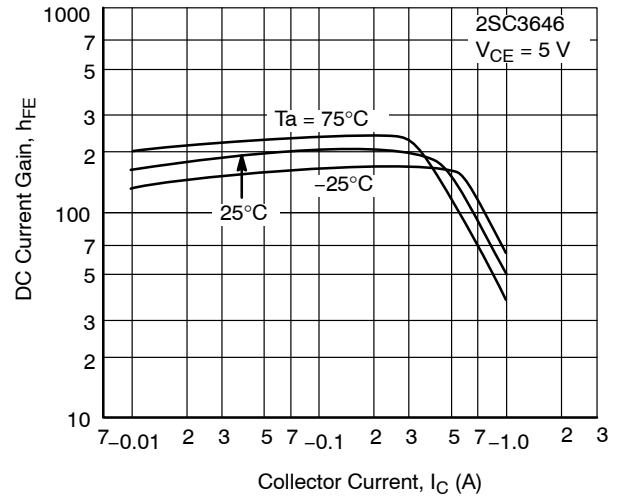


Figure 8. $h_{FE} - I_C$

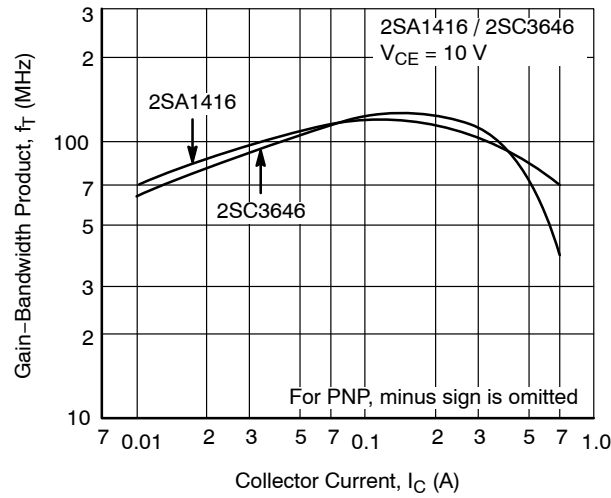


Figure 9. $f_T - I_C$

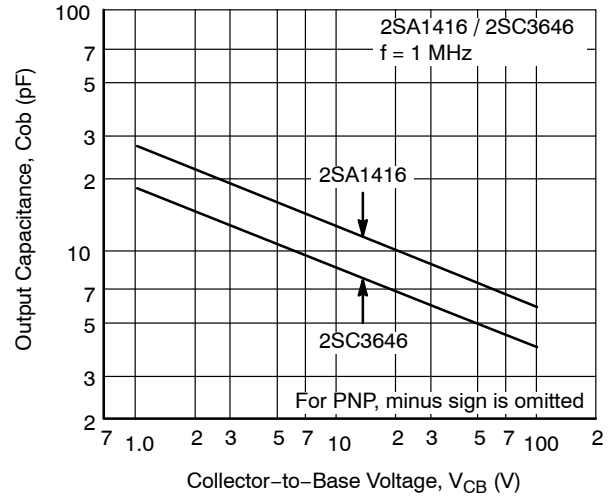


Figure 10. $C_{ob} - V_{CB}$

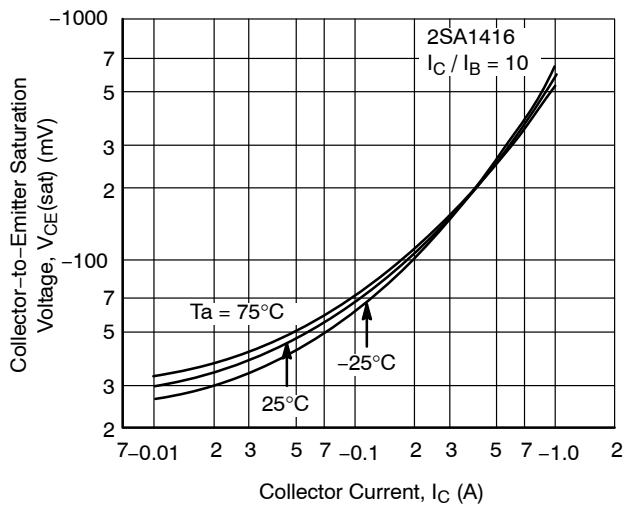


Figure 11. $V_{CE(sat)} - I_C$

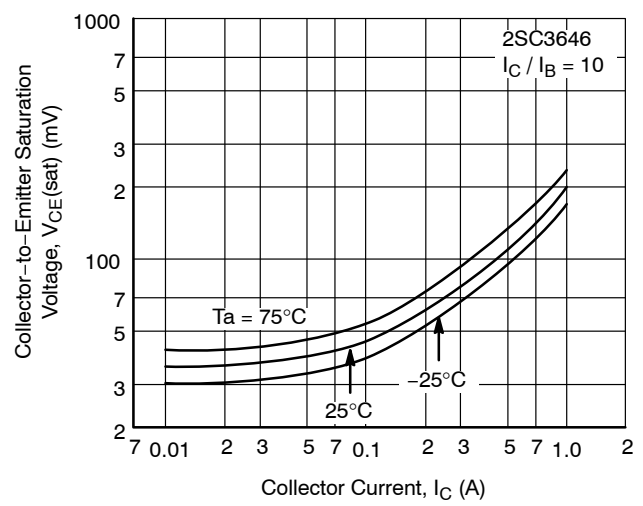


Figure 12. $V_{CE(sat)} - I_C$

TYPICAL CHARACTERISTICS (continued)

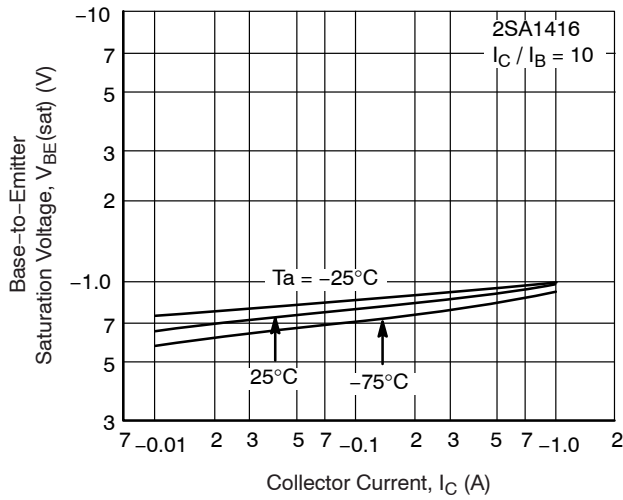


Figure 13. $V_{BE(sat)} - I_C$

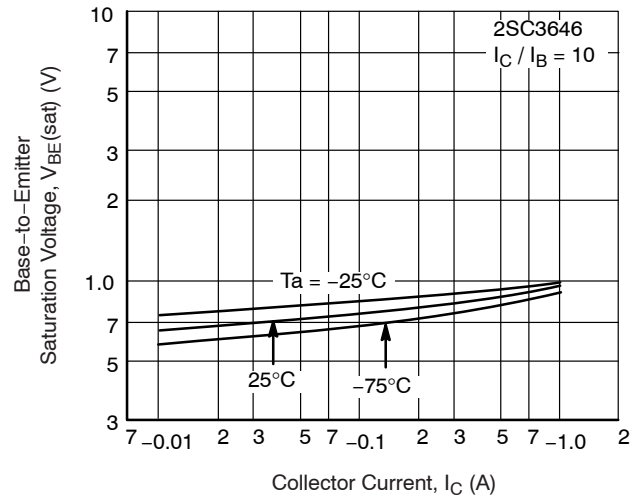


Figure 14. $V_{BE(sat)} - I_C$

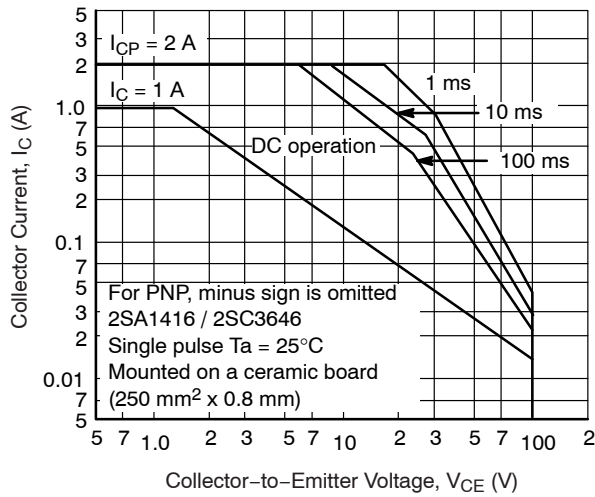


Figure 15. ASO

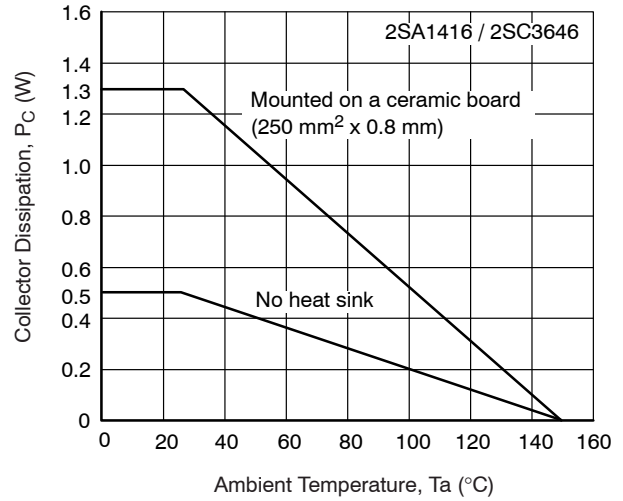


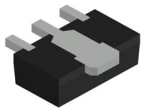
Figure 16. $P_C - T_a$

2SA1416, 2SC3646

ORDERING INFORMATION

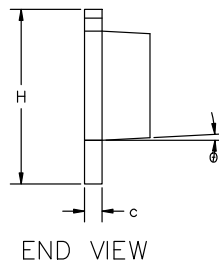
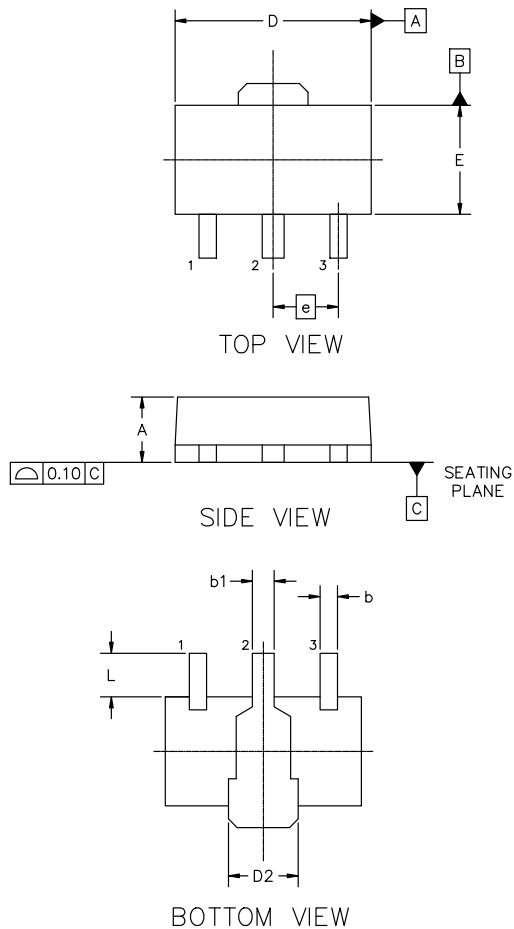
Device	Marking	Package	Shipping [†]
2SA1416S–TD–E	AB	SOT–89 / PCP–1 (Pb–Free)	1000 / Tape & Reel
2SA1416T–TD–E			
2SC3646S–TD–E	CB		
2SC3646T–TD–E			

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



SOT-89 4.50x2.50x1.50 1.50P
CASE 419AU
ISSUE A

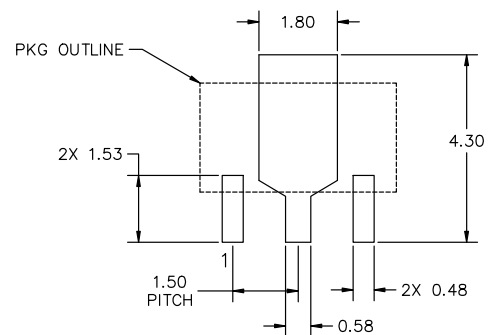
DATE 21 MAY 2025



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. LEAD THICKNESS INCLUDES LEAD FINISH.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

MILLIMETERS			
DIM	MIN	NOM	MAX
A	1.40	1.50	1.60
b	0.35	0.40	0.48
b1	0.40	0.50	0.55
c	0.37	0.40	0.43
D	4.40	4.50	4.60
D2	1.40	1.60	1.80
E	2.40	2.50	2.60
e	1.50 BSC		
H	3.80	4.00	4.20
L	0.80	1.00	1.20
θ	0°	---	3°



RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

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DESCRIPTION:	SOT-89 4.50x2.50x1.50 1.50P	PAGE 1 OF 1

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